

2MBI300VH-170-50

IGBT Modules

IGBT MODULE (V series) 1700V / 300A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T_c=25°C unless otherwise specified)



Items	Symbols	Conditions	Conditions		Units		
Collector-Emitter voltage	Vces		,	1700	V		
Gate-Emitter voltage	V _{GES}			±20	V		
Collector current	Ic	Continuous	Tc=100°C	300			
		Continuous	Tc=25°C	440			
	I _{C pulse}	1ms		600	Α		
	- I c			300			
	-IC pulse	1ms	1ms				
Collector power dissipation	Pc	1 device	1 device		W		
Junction temperature	T _j		'	175	°C		
Operating junction temperature (under switching conditions)	T _{jop}			150			
Case temperature	Tc			125			
Storage temperature	T _{stg}						
Isolation voltage between terminal and copper base (*1)	Viso	AC: 1min.	AC : 1min.		4000		VAC
Screw torque Mounting (*2)	-			6.0	N m		
Terminals (*3)	-			5.0	IN III		

Note *1: All terminals should be connected together during the test.

Note *2: Recommendable Value : 3.0-6.0 N·m (M5 or M6) Note *3: Recommendable Value : 2.5-5.0 N·m (M5)

● Electrical characteristics (at T_i= 25°C unless otherwise specified)

lt	Cympholo	Canditions	41		Characteristics		
Items	Symbols	Conditions		min.	typ.	max.	Units
Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1700V		-	-	2.0	mA
Gate-Emitter leakage current	Iges	$V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	400	nA
Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 300mA		6.0	6.5	7.0	V
Collector-Emitter saturation voltage	V	V _{GE} = 15V	T _j =25°C	-	2.15	2.60	V
	VCE (sat)		T _j =125°C	-	2.55	-	
	(terminal)		T _j =150°C	-	2.60	-	
	V	Ic = 300A	T _j =25°C	-	2.00	2.45	
	V _{CE} (sat)		T _j =125°C	-	2.40	-	
	(chip)		T _j =150°C	-	2.45	-	
Internal gate resistance	R _G (int)	-		-	2.5	-	Ω
Input capacitance	Cies	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	33	-	nF
Turn-on time	ton	V_{CC} = 900V, I_{C} = 300A V_{GE} = ±15V, Rg_on= 4.7 Ω , Rg_off= 2.4 Ω T_{J} =150°C, L_{S} = 30nH		-	1150	-	nsec
	tr			-	580	-	
	t _{r (i)}			-	60	-	
Turn-off time	toff			-	1050	-	
	tr			-	140	-	
Forward on voltage	V	V _{GE} = 0V I _F = 300A	T _j =25°C	-	1.95	2.40	- V
	(terminal)		T _j =125°C	-	2.15	-	
	(terminal)		T _j =150°C	-	2.15	-	
	VF		T _j =25°C	-	1.80	2.25	
	1		T _j =125°C	-	2.05	-	
	(chip)		T _j =150°C	-	2.05	-	
Reverse recovery time	trr	I _F = 300A		-	220	-	nsec

Thermal resistance characteristics

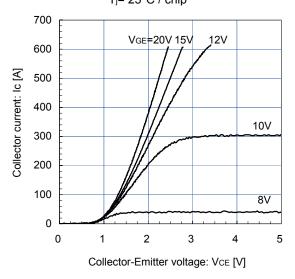
Items	Symbols	Conditions	Characteristics			Units	
items			min.	typ.	max.	Units	
Thermal resistance(1device)	R _{th(j-c)}	IGBT	-	-	0.083	°C/W	
		FWD	-	-	0.130		
Contact thermal resistance (1device) (*4)	R _{th(c-f)}	with Thermal Compound	-	0.0125	_		

Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

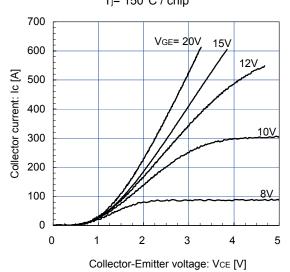
■ Characteristics (Representative)

Collector current vs. Collector-Emitter voltage (typ.)

Tj= 25°C / chip

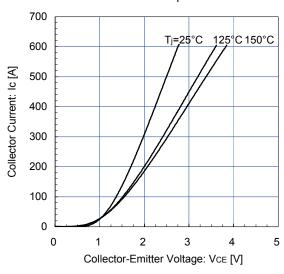


Collector current vs. Collector-Emitter voltage (typ.) T_j = 150°C / chip

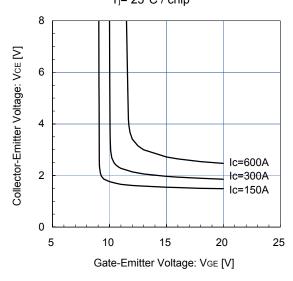


Collector current vs. Collector-Emitter voltage (typ.)

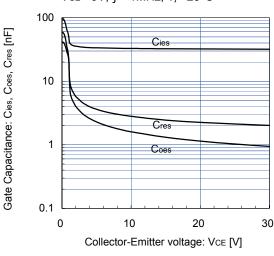
VGE= 15V / chip



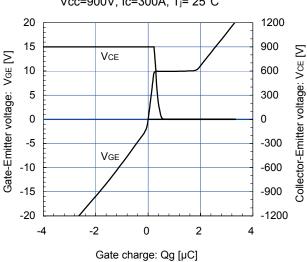
Collector-Emitter voltage vs. Gate-Emitter voltage T_j= 25°C / chip



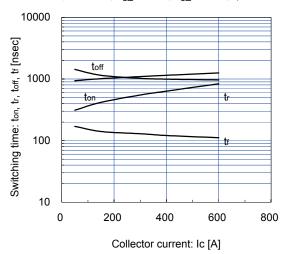
Gate Capacitance vs. Collector-Emitter Voltage VGE= 0V, f= 1MHz, Tj= 25°C



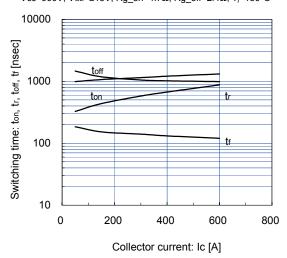
Dynamic Gate Charge (typ.) Vcc=900V, Ic=300A, T_j= 25°C



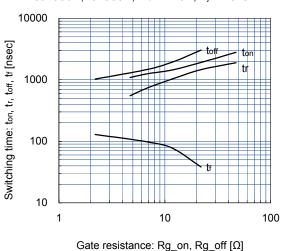
Switching time vs. Collector current (typ.) Vcc=900V, VgE= \pm 15V, Rg_on= \pm 4.7Q, Rg_off= \pm 2.4Q, Tj=125°C



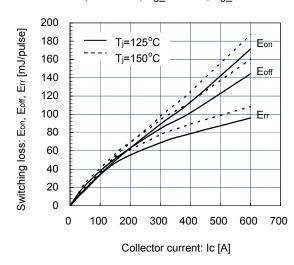
Switching time vs. Collector current (typ.) Vcc=900V, Vge= \pm 15V, Rg_on= 4.7Ω , Rg_off= 2.4Ω , Tj=150°C



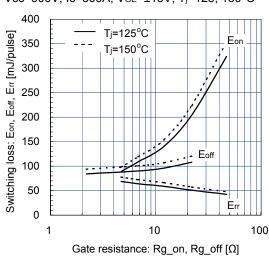
Switching time vs. Gate resistance (typ.) Vcc=900V, Ic=300A, VGE=±15V, Ti=125°C



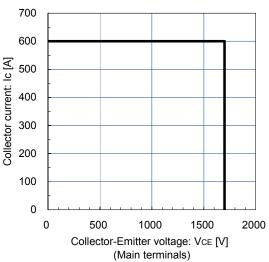
Switching loss vs. Collector current (typ.) Vcc=900V, V_{GE}= \pm 15V, Rg_on= 4.7Ω , Rg_off= 2.4Ω



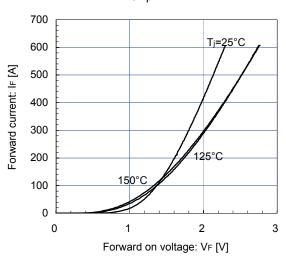
Switching loss vs. Gate resistance (typ.) Vcc=900V, Ic=300A, VgE=±15V, Tj=125, 150°C



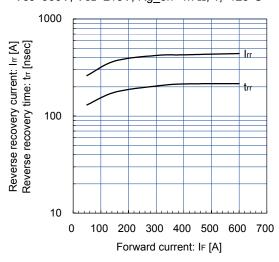
Reverse bias safe operating area (max.) +VGE=15V, -VGE=15V, Rg_off=2.4 Ω , Tj=150°C



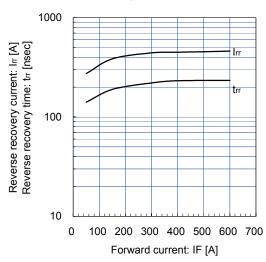
Forward Current vs. Forward Voltage (typ.) chip



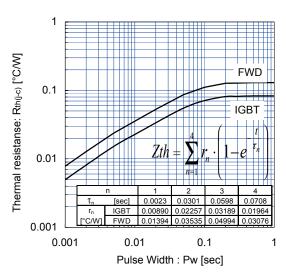
Reverse Recovery Characteristics (typ.) Vcc=900V, $VgE=\pm15V$, $Rg_on=4.7\Omega$, $T_j=125^{\circ}C$



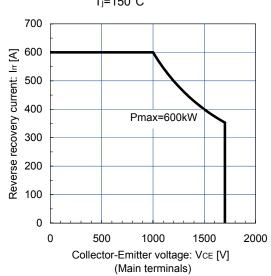
Reverse Recovery Characteristics (typ.) Vcc=900V, $VgE=\pm15V$, $Rg_on=4.7\Omega$, $Tj=150^{\circ}C$



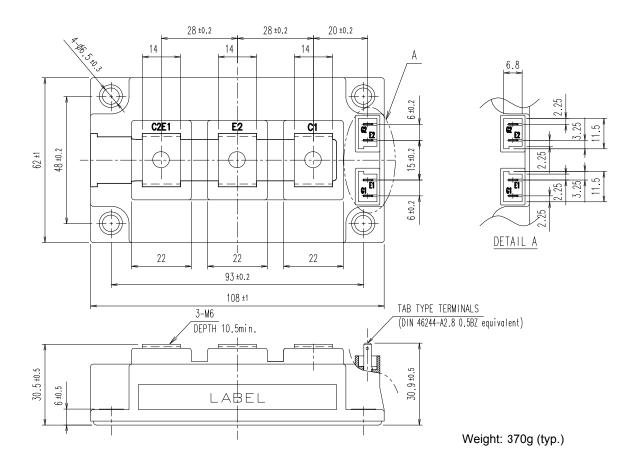
Transient Thermal Resistance (max.)



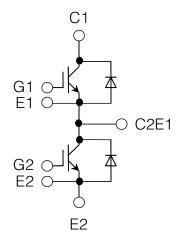
FWD safe operating area (max.) $T_i=150$ °C



■ Outline Drawings, mm



■ Equivalent Circuit Schematic



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- · Measurement equipment

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